AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): A semiconductor light emitting device comprising:

an active layer composed of a nitride based semiconductor;

a cladding layer formed on said active layer, composed of a nitride based semiconductor of a first conductivity type, and having a flat portion and a ridge portion formed on the flat portion;

a first current blocking layer formed on said flat portion and on sidewalls of said ridge portion of said cladding layer and composed of a high-resistive nitride based semiconductor containing impurities; and

a second current blocking layer formed on said first current blocking layer and composed of a nitride based semiconductor of a second conductivity type opposite to said first conductivity type:

wherein the cladding layer is composed of AlGaN;

wherein the first current blocking layer is composed of AlGaN having a larger Al composition ratio than that of the cladding layer; and

wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon;

~~a second current blocking layer formed on said first current blocking layer and~~

~~composed of a nitride based semiconductor of a second conductivity type opposite to said first conductivity type;~~

~~wherein the cladding layer is composed of AlGaN;~~

~~wherein the first current blocking layer is composed of AlGaN having a larger Al composition ratio than that of the cladding layer; and~~

~~wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon.~~

Claim 2 (canceled)

Claim 3 (original): The semiconductor light emitting device according to claim 1, wherein said first current blocking layer has a resistance value of not less than 1.5 Ω·cm

Claim 4 (canceled)

Claim 5 (original): The semiconductor light emitting device according to claim 1, wherein the thickness of said first current blocking layer is not less than 0.5 μm.

Claim 6 (original): The semiconductor light emitting device according to claim 5, wherein the thickness of said first current blocking layer is not less than 1.0 μm.

Claim 7 (original): The semiconductor light emitting device according to claim 1, wherein the thickness of the flat portion of said cladding layer is not more than 0.3 μm.

Claim 8 (currently amended): The semiconductor light emitting device according to claim 7, ~~whereinthe~~ wherein the thickness of the flat portion of said cladding layer is not more than 0.08 μm.

Claim 9 (original): The semiconductor light emitting device according to claim 1, wherein said nitride based semiconductor contains at least one of boron, gallium, aluminum, indium, and thallium.

Claim 10 (currently amended): [[A]] The semiconductor light emitting device according to claim 1, wherein ~~comprising:~~

~~an active layer composed of a nitride based semiconductor;~~

~~a cladding layer formed on said active layer, composed of a nitride based semiconductor of a first conductivity type, and having a flat portion and a ridge portion formed on the flat portion,~~ said cladding layer having a recess on said flat portion along both sidewalls of said ridge portion; and

[[a]] said first current blocking layer is formed on said flat portion and on the sidewalls of said ridge portion ~~of said cladding layer and composed of a high-resistive nitride based semiconductor containing impurities~~ such that it is embedded in said recess of said cladding layer.~~;~~

~~and~~

~~a second current blocking layer formed on said first current blocking layer and composed of a nitride based semiconductor of a second conductivity type opposite to said first conductivity type:~~;

~~wherein the cladding layer is composed of AlGaN; and~~

~~wherein the first current blocking layer is composed of AlGaN having a larger Al composition ratio than that of the cladding layer;~~

~~wherein said first current blocking layer is composed of a high resistive nitride based semiconductor containing impurities: and~~

~~wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon~~.

Claims 11-19 (canceled)